

FERROELECTRIC MEMORY DEVICE, METHOD OF MANUFACTURING THE SAME,

AND EMBEDDED DEVICE

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PAT. 6,727,536 >

The present application includes the entire content of

5 Japanese Patent Application No. 2000-281725 filed on September  
18, 2000.

FIELD OF THE INVENTION

The present invention relates to a ferroelectric memory  
10 device, a method of manufacturing the same, and an embedded  
device. More particularly, the present invention relates to  
a simple matrix ferroelectric memory device using only  
ferroelectric capacitors instead of cell transistors, a method  
of manufacturing the same, and an embedded device.

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BACKGROUND OF ART

A simple matrix memory cell array using only ferroelectric  
capacitors instead of cell transistors has a very simple  
structure and enables a higher degree of integration.  
20 Therefore, development of such a memory cell array has been  
expected.

SUMMARY

An objective of the present invention is to provide a  
25 ferroelectric memory device including a desired memory cell  
array, a method of manufacturing the same, and an embedded  
device.